

FORM PTO-1449 SAMUELS, GAUTHIER & STEVENS LLP  
(Rev. 5/92) 225 Franklin Street, Boston, MA 02110  
Telephone: (617) 426-9189

MIT.9944  
ATTORNEY DOCKET NO.

10/632,442  
SERIAL NO.

APPLICANT: McGill et al.

GROUP: 2811

FILING DATE: August 1, 2003

EXAMINER: Unknown

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA	2001/0028061	10/11/2001	Hosoba et al.			03/29/2001
	AB	6,108,360	08/22/2000	Razeghi			06/06/1997
	AC						
	AD						
	AE						
	AF						
	AG						

**FOREIGN PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	AH						

**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
	AJ	"Evolution of microstructure and dislocation dynamics in $\text{In}_x\text{Ga}_{1-x}\text{P}$ graded Buffers grown on GaP by metalorganic vapor phase epitaxy: engineering device-quality substrate materials," Kim et al. <i>J. Vac. Sci. Technol. B</i> . Jul/Aug 1999. Vol. 17.
	AJ	"Yellow-Green emission for ETS-LEDs and Lasers based on a strained InGaP quantum well heterostructure grown on a transparent, compositionally graded AlInGaP buffer," McGill et al. <i>Mat. Res. Soc. Symp.</i> 2003: Vol. 744.
	AK	
	AL	
	AM	
	AN	

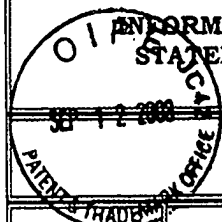
EXAMINER

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Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA						
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	AH						

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
	AI	"Gas-Source Molecular Beam Epitaxial Growth, Characterization, and Light-Emitting diode application of $\text{In}_x\text{Ga}_{1-x}\text{P}$ on $\text{GaP}(100)$ ," Chin et al. <i>Applied Physics Letters</i> . May 1993. Vol. 62, No. 19.
	AJ	"Highly Strained $\text{In}_x\text{Ga}_{1-x}\text{P}/\text{GaP}$ Quantum Wells Grown on $\text{GaP}$ and on an $\text{In}_{x/2}\text{Ga}_{1-x/2}\text{P}$ Buffer Layer by Gas-Source Molecular Beam Epitaxy," Bi et al. <i>Journal of Crystal Growth</i> . 1996. Vol. 165.
	AK	
	AL	
	AM	
	AN	

EXAMINER <i>Jackson</i>	DATE CONSIDERED 1/05
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EXAMINER: <i>Jackson</i>	Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.
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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA	6,064,076	05/16/2000	Chen et al.			05/20/1998
	AB	5,751,753	05/12/1998	Uchida			07/23/1996
	AC	6,433,364	08/13/2002	Hosoba et al.			03/29/2001
	AD	6,081,540	06/27/2000	Nakatsu			12/18/1997
	AE	5,300,794	04/05/1994	Melman et al			03/19/1991
	AF	5,363,392	11/08/1994	Kasukawa et al.			11/18/1992
	AG						

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	AH						

**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
	AI	"Growth and Characterization of InGaP Yellow-Green Light-Emitting Diodes by Liquid-Phase Epitaxy," Chen et al. <i>Japanese Journal of Applied Physics</i> . January 1992. Vol. 31.
	AJ	"High-Efficiency InGaP Light-Emitting Diodes on GaP Substrates," Stinson et al. <i>Applied Physics Letters</i> . May 1991. Vol. 58, No. 18.
	AK	"AlGaInP/GaInP Double-Heterostructure Orange Light-Emitting Diodes on GaAsP Substrates Prepared by Metalorganic Vapor-Phase Epitaxy," Lin et al. <i>Journal of Crystal Growth</i> . 1994. Vol. 137.
	AL	"Metalorganic Vapor Phase Epitaxy Growth and Characterization of (Al <sub>x</sub> Ga <sub>1-x</sub> ) <sub>0.5</sub> In <sub>0.5</sub> P/Ga <sub>0.5</sub> In <sub>0.5</sub> P (x=0.4, 0.7, and 1.0) Quantum Wells on 15°-Off-(100) GaAs Substrates at High Growth Rate," Jou et al. <i>Japanese Journal of Applied Physics</i> . October 1993. Vol. 32, No. 10.
	AM	"Yellow-Green Emission for ETS-LEDs and lasers based on a strained-InGaP quantum well heterostructure grown on a transparent, compositionally graded AlInGaP buffer," McGill et al. <i>Mat. Res. Symp. Proc.</i> 2003. Vol. 744
	AN	"Growth and Characterization of Lattice-Mismatched In <sub>x</sub> Ga <sub>1-x</sub> P Yellow Light Emitting Diodes on GaP," Paul Liu, Phd. Thesis, University of Illinois. 1997.

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DATE CONSIDERED

7/05

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Initial if citati n c nsidered, wh ther r n t citati n is in c nf rmance with MPEP 609; draw line thr ugh citation if n t in c nf rmance and n t c nsidered. Include c py f this f rm with next c mmunication to applicant.